

In th Sp cification

On page 1, before the section entitled "Technical Field", please insert the following:

--RELATED PATENT DATA

This patent resulted from a continuation application of U.S. Patent Application Serial No. 09/994,894, filed August 31, 2001, entitled "Method of Forming a Local Interconnect", naming H. Montgomery Manning as inventor, now abandoned, the disclosure of which is incorporated by reference; which patent resulted from a divisional application of U.S. Patent Application Serial No. 09/608,333, filed June 29, 2000, entitled "Method of Fabricating Integrated Circuitry", naming H. Montgomery Manning as inventor, now U.S. Patent No. 6,391,726 B1, the disclosure of which is incorporated by reference; which patent resulted from a divisional application of U.S. Patent Application Serial No. 09/266,456, filed March 11, 1999, entitled "Integrated Circuitry, Methods of Fabricating Integrated Circuitry, Methods of Forming Local Interconnects, and Methods of Forming Conductive Lines", naming H. Montgomery Manning as inventor, now U.S. Patent No. 6,180,494, the disclosure of which is incorporated by reference.

Please replace the paragraph beginning at line 13 on page 8 with the following:

After etching of layer 34, at least one of the exposed sidewalls is covered with insulating material. Such preferably comprises deposition of an insulating layer 46 over substrate 12; lines 22, 24 and 26; and planarized and etched insulative material 34 to a thickness which less than completely fills at least some of the contact openings (Fig. 6). Such layer preferably comprises a spacer forming layer, with silicon dioxide and silicon nitride being but two examples.

Please replace the paragraph beginning at line 16 on page 11 with the following:

Referring to Fig. 9, local interconnect layer 56 is formed (i.e., by photopatterning and etching) into a local interconnect line 57 which overlies at least portions of illustrated conductive lines 24, 26 and 28 22, 24 and 26, and electrically interconnects substrate material locations 42, 43 and 44.